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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/711,043	08/19/2004	Shaun Crawford	BUR920040095US1 5042		
44152 7.	590 01/10/2006		EXAMINER		
GREENBLUM & BERNSTEIN, P.L.C. 1950 ROLAND CLARK DRIVE			GREEN, PHILLIP		
RESTON, VA 20191			ART UNIT	PAPER NUMBER	
•			2823		
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Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	10/711,043	CRAWFORD ET AL.	
Office Action Summary	Examiner	Art Unit	
	Phillip S. Green	2823	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period value of the period for reply within the set or extended period for reply will, by statute any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be timed will expire SIX (6) MONTHS from a cause the application to become ABANDONE	I. nely filed the mailing date of this communication. D (35 U.S.C. § 133).	
Status			
1) ☐ Responsive to communication(s) filed on 19 At 2a) ☐ This action is FINAL.  2b) ☐ This 3) ☐ Since this application is in condition for alloward closed in accordance with the practice under Expression in the practice of the closed in accordance with the practice of the closed in accordance with the practice under Expression is accordance.	action is non-final.  nce except for formal matters, pro		
Disposition of Claims			
4) Claim(s) 1-20 is/are pending in the application.  4a) Of the above claim(s) is/are withdray  5) Claim(s) is/are allowed.  6) Claim(s) 1-20 is/are rejected.  7) Claim(s) is/are objected to.  8) Claim(s) are subject to restriction and/o	wn from consideration. r election requirement.		
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acceptable and applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine 10.	epted or b) objected to by the formal drawing(s) be held in abeyance. See this is required if the drawing(s) is objected to by	e 37 CFR 1.85(a). sected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign  a) All b) Some * c) None of:  1. Certified copies of the priority document  2. Certified copies of the priority document  3. Copies of the certified copies of the priority document  application from the International Bureau  * See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage	
Attachment(s)  1) Notice of References Cited (PTO-892)	4) Interview Summary	•	
<ol> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)         Paper No(s)/Mail Date <u>08/19/04</u>, <u>08/3004/</u>.     </li> </ol>	Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate atent Application (PTO-152)	

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#### **DETAILED ACTION**

#### Information Disclosure Statement

1. The information disclosure statement (IDS) submitted on 08/19/2004 and 08/30/2004 was filed after the mailing date of the application on 08/19/2004. The submission is in compliance with the provisions of 37 CFR 1.97. Accordingly, the information disclosure statement is being considered by the examiner.

## **Drawings**

The drawings are objected to as failing to comply with 37 CFR 1.84(p)(4) because reference characters "14" and "19" have both been used to designate opaque material. Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

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## Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 3. Claims 1-8 are rejected under 35 U.S.C. 102(e) as being anticipated by Hamada et al. (US 2004/0241579 A1).

Pertaining to claim 1, <u>Hamada</u> discloses a method of photoresist trimming, comprising the steps of:

forming a resist foot in a trench; and

removing the resist foot found in the trench during a trimming process. (Note: Paragraph 0192-0194. As stated in the applicant's paragraph 0004, a mask foot is an extension of mask material extending from a mask sidewall into the opening in the mask bound by the sidewall and is an unwanted resist or scum forming a generally sloping structure on the sidewall. Hamada in Paragraph 0193 discloses an uneven, unwanted scum on the edge of the organic sidewall. The examiner takes the position the scum removed in Hamada in order to smooth the edge line is a resist foot.).

Pertaining to claim 2, <u>Hamada</u> discloses the above limitations of claim 1 above, including, wherein the trimming step comprises ionizing a portion of a mixture of gases

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comprising O<sub>2</sub> and at least one other oxide gas to form an etchant for the trimming process. (Note: Paragraph 0192-0194).

Pertaining to claim 3, <u>Hamada</u> discloses the above limitations of claim 2 above, including, wherein the mixture of gases comprises any of at least CO<sub>2</sub>, SO<sub>2</sub> and NO<sub>2</sub> formed by mixing during a plasma etching process. (Note: Paragraph 0192-0194).

Pertaining to claim 4, <u>Hamada</u> discloses the above limitations of claim 2 above, including, wherein the trimming process is performed on a mask and an upper surface of the mask is resistant to etching. (Note: Paragraph 0016-0019).

Pertaining to claim 5, <u>Hamada</u> discloses the above limitations of claim 4 above, including, polymerizing an upper surface of the mask. (Note: Paragraph 0016-0019).

Pertaining to claim 6, <u>Hamada</u> discloses the above limitations of claim 3 above, including, comprising providing a barrier on an upper surface of the mask derived from an oxide gas. (Note: Paragraph 0016-0019).

Pertaining to claim 7, <u>Hamada</u> discloses the above limitations of claim 3 above, including, arranging a carbon barrier on an upper surface of the mask. (Note: Paragraph 0192-0194).

Pertaining to claim 8, <u>Hamada</u> discloses the above limitations of claim 1 above, including, forming a sidewall in a mask which is to be trimmed during the trimming step, and etching a lower portion of the sidewall of the mask using the mixture of gases comprising O<sub>2</sub> and at least one other oxide gas to form the sidewall substantially perpendicular to a surface of the mask. (Note: Fig. 2).

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4. Claims 18-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Vaartstra (US 6,242,165 B1).

Pertaining to claim 18, <u>Vaartstra</u> discloses a trim gas for etching a mask foot formed at a base of a sidewall pattern, comprising O<sub>2</sub> and at least one other oxide gas comprising at least any one of CO<sub>2</sub>, SO<sub>2</sub>, and NO<sub>2</sub>. (Note: Column 5, line 19 – Column 6, line 10).

Pertaining to claim 19, Vaartstra discloses the above limitations of claim 18 above, including, the O<sub>2</sub> and at least one other oxide gas has a pressure ranging from about 1mT to 1000 mT. (Note: Column 5, line 19 – Column 6, line 10).

Pertaining to claim 20, Vaartstra discloses the above limitations of claim 18 above, including, the O<sub>2</sub> and at least one other oxide gas is configured to strengthen an upper surface of a photoresist being trimmed. (Note: Column 6, lines 11-22).

## Claim Rejections - 35 USC § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claims 9-13 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hamada (US 2004/0241579 A1) in view of Vaartstra (US 6,242,165 B1).

Pertaining to claim 9, <u>Hamada</u> discloses the limitations of claim 2 in Paragraph 3 above.

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<u>Hamada</u> specifically fails to disclose the mixture of gases comprising  $O_2$  and at least one other oxide gas in a ratio ranging from about 1:50 to 50:1.

<u>Vaarstra</u> teaches the ratio of the oxidizer component to the additional component in the supercritical state is in the range of 1:100 by volume to about 100:1 by volume. (Note: Column 6, lines 8-10).

Both Hamada and <u>Vaarstra</u> teach the removal of photoresist residue, therefore, they are analogues.

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to provide the composition of gas as taught by <u>Vaartstra</u> to the invention of <u>Hamada</u> in order to achieve effective removal of organic materials. (Vaartstra, Col. 2, line 56-57).

Generally, differences in concentration or temperature will not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955) (Claimed process which was performed at a temperature between 40°C and 80°C and an acid concentration between 25% and 70% was held to be prima facie obvious over a reference process which differed from the claims only in that the reference process was performed at a temperature of 100°C and an acid concentration of 10%.)

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Pertaining to claim 10, <u>Hamada</u> discloses the limitations of in claim 2 Paragraph 3 above.

Hamada specifically fails to disclose the mixture of gases comprising O<sub>2</sub> and at least one other oxide gas in a ratio ranging from about 1:10 to 10:1.

<u>Vaarstra</u> teaches the ratio of the oxidizer component to the additional component in the supercritical state is in the range of 1:100 by volume to about 100:1 by volume. (Note: Column 6, lines 8-10).

Both Hamada and <u>Vaarstra</u> teach the removal of photoresist residue, therefore, they are analogues.

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to provide the composition of gas as taught by <u>Vaartstra</u> to the invention of <u>Hamada</u> in order to achieve effective removal of organic materials. (Vaartstra, Col. 2, line 56-57).

Generally, differences in concentration or temperature will not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955) (Claimed process which was performed at a temperature between 40°C and 80°C and an acid concentration between 25% and 70% was held to be prima facie obvious over a reference process which differed from the claims only in

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that the reference process was performed at a temperature of 100°C and an acid concentration of 10%.).

Pertaining to claim 11, <u>Hamada</u> discloses the limitations of claim 10 above.

<u>Hamada</u> specifically fails to disclose the mixture of gases comprising  $O_2$  and at least one other oxide gas in a ratio ranging from about 1:3 to 3:1.

<u>Vaarstra</u> teaches the ratio of the oxidizer component to the additional component in the supercritical state is in the range of 1:100 by volume to about 100:1 by volume. (Note: Column 6, lines 8-10)

Both Hamada and <u>Vaarstra</u> teach the removal of photoresist residue, therefore, they are analogues.

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to provide the composition of gas as taught by <u>Vaartstra</u> to the invention of <u>Hamada</u> in order to achieve effective removal of organic materials. (Vaartstra, Col. 2, line 56-57).

Generally, differences in concentration or temperature will not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955) (Claimed process which was performed at a temperature between 40°C and 80°C and an acid concentration between 25% and 70% was held to be prima facie obvious over a reference process which differed from the claims only in

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that the reference process was performed at a temperature of 100°C and an acid concentration of 10%.)

Pertaining to claim 12, <u>Hamada</u> discloses the limitations of claim 2 in Paragraph 3 above.

Hamada specifically fails to disclose holding the mixture of gases comprising O<sub>2</sub> and at least one other oxide gas at a pressure ranging from about 1 mT to 1000 mT.

<u>Vaarstra</u> teaches the chamber at a pressure above the critical temperature. (Column 10, lines 22-24).

Both Hamada and <u>Vaarstra</u> teach the removal of photoresist residue, therefore, they are analogues.

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to provide the composition of gas as taught by <u>Vaartstra</u> to the invention of <u>Hamada</u> in order to achieve effective removal of organic materials. (Vaartstra, Col. 2, line 56-57).

Notwithstanding, it would have been an obvious matter of design choice bounded by well known manufacturing constraints and ascertainable by routine experimentation and optimization to choose these particular dimensions because applicant has not disclosed that the dimensions are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical, and it appears prima facie that the process would possess utility using another dimension. Indeed, it has been held that mere dimensional limitations are prima facie obvious absent a disclosure that the limitations are for a particular unobvious purpose, produce an unexpected result, or are otherwise

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critical. See, for example, *In re Rose*, 220 F.2d 459, 105 USPQ 237 (CCPA 1955); *In re Rinehart*, 531 F.2d 1048, 189 USPQ 143 (CCPA 1976); *Gardner v. TEC Systems, Inc.*, 725 F.2d 1338, 220 USPQ 777 (Fed. Cir. 1984), cert. denied, 469 U.S. 830, 225 USPQ 232 (1984); *In re Dailey*, 357 F.2d 669, 149 USPQ 47 (CCPA 1966.

Pertaining to claim 13, <u>Hamada</u> discloses the limitations of claim 2 in Paragraph 3 above.

Hamada specifically fails to disclose the forming the trimming gas comprises mixing O<sub>2</sub> and at least one other oxide gas at a pressure ranging from about 1 mT to 100 mT.

<u>Vaarstra</u> teaches the chamber at a pressure above the critical temperature. (Column 10, lines 22-24).

Both <u>Hamada</u> and <u>Vaarstra</u> teach the removal of photoresist residue, therefore, they are analogues.

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to provide the composition of gas as taught by <u>Vaartstra</u> to the invention of <u>Hamada</u> in order to achieve effective removal of organic materials. (Vaartstra, Col. 2, line 56-57).

Notwithstanding, it would have been an obvious matter of design choice bounded by well known manufacturing constraints and ascertainable by routine experimentation and optimization to choose these particular dimensions because applicant has not disclosed that the dimensions are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical, and it appears prima facie that the process

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would possess utility using another dimension. Indeed, it has been held that mere dimensional limitations are prima facie obvious absent a disclosure that the limitations are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical. See, for example, *In re Rose*, 220 F.2d 459, 105 USPQ 237 (CCPA 1955); *In re Rinehart*, 531 F.2d 1048, 189 USPQ 143 (CCPA 1976); *Gardner v. TEC Systems, Inc.*, 725 F.2d 1338, 220 USPQ 777 (Fed. Cir. 1984), cert. denied, 469 U.S. 830, 225 USPQ 232 (1984); *In re Dailey*, 357 F.2d 669, 149 USPQ 47 (CCPA 1966).

7. Claims 14-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Deng et al. (US 2005/0045799 A1) in view of Vaartstra (US 6,242,165 B1).

Pertaining to claim 14, <u>Deng</u> discloses a method of forming an imaging mask, comprising the steps of:

arranging an opaque layer on a transparent substrate (120); arranging a mask material (141) on the opaque layer (Note: Para. 0115); imaging the mask with a prescribed pattern; and (Note: Para. 0085) trimming an etched mask with a trimming gas comprising O<sub>2</sub>. (Note: Para 0115).

However, <u>Deng</u> does not teach the step of trimming an etched mask with a trimming gas comprising O<sub>2</sub> and at least one other oxide gas.

Vaartstra discloses the step of trimming an etched mask with a trimming gas comprising O<sub>2</sub> and at least one other oxide gas.

Therefore, it would have been obvious to one having ordinary skill in the art at the time of applicant(s) claimed invention was made to use O<sub>2</sub> and at least one other

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oxide gas to remove organic residue from a variety of substrate. (Note: Vaartstra, Col 2, line 27-54).

Pertaining to claim 15, <u>Deng</u> and <u>Vaartstra</u> disclose the limitations of claim 14 in the paragraph above, including, the ratio of the oxidizer component to the additional component in the supercritical state is in the range of 1:100 by volume to about 100:1 by volume. (Note: Vaartstra, Column 6, lines 8-10).

Pertaining to claim 16, <u>Deng</u> and <u>Vaartstra</u> disclose the limitations of claim 14 above, including, forming the trimming gas comprises mixing O<sub>2</sub> and at least one other oxide gas at a pressure ranging from about 1 mT to 100 mT. (Vaartstra, Column 10, lines 22-24).

Pertaining to claim 17, <u>Deng</u> and <u>Vaartstra</u> disclose the above limitations of claim 14 above, including, the imaging step includes the formation of a mask foot at a based of the prescribed pattern and the trimming step includes removal of the mask foot to form substantially perpendicular sidewalls of the prescribed pattern with respect to a surface thereof. (Note: Deng, Fig 3).

# Correspondence

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Phillip S. Green whose telephone number is (571) 272-7024. The examiner can normally be reached on Monday thru Thursday 8:30 am to 6:00 pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, Note http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

PG 12/28/2005 BROOK KEBEDE PRIMARY EXAMINER